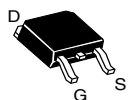
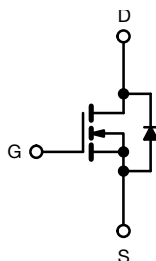
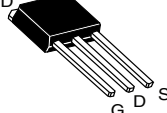


Power MOSFET

DPAK
(TO-252)

IPAK
(TO-251)


N-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Surface-mount (IRFR210, SiHFR210)
- Straight lead (IRFU210, SiHFU210)
- Available in tape and reel
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available

PRODUCT SUMMARY

V_{DS} (V)	200	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	1.5
Q_g max. (nC)	8.2	
Q_{gs} (nC)	1.8	
Q_{gd} (nC)	4.5	
Configuration	Single	

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU, SiHFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface mount applications.

ORDERING INFORMATION

PACKAGE	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)
Lead (Pb)-free and halogen-free	SiHFR210-GE3	SiHFR210TRL-GE3 ^a	-	SiHFR210TRR-GE3 ^a	SiHFU210-GE3
Lead (Pb)-free	IRFR210PbF	IRFR210TRLPbF ^a	IRFR210TRPbF ^a	IRFR210TRRPbF	IRFU210PbF
Lead (Pb)-free and halogen-free	IRFR210PbF-BE3 ^{ab}	IRFR210TRLPbF-BE3 ^{ab}	IRFR210TRPbF-BE3 ^{ab}	-	-

Notes

- a. See device orientation
b. "-BE3" denotes alternate manufacturing location

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	200	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A
		$T_C = 100\text{ }^\circ\text{C}$	
Pulsed drain current ^a	I_{DM}	10	W/ $^\circ\text{C}$
Linear derating factor		0.20	
Linear derating factor (PCB mount) ^e		0.020	
Single pulse avalanche Energy ^b	E_{AS}	95	mJ
Avalanche current ^a	I_{AR}	2.7	A
Repetitive avalanche energy ^a	E_{AR}	2.5	mJ
Maximum power dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	W
Maximum power dissipation (PCB mount) ^e		$T_A = 25\text{ }^\circ\text{C}$	
Peak diode recovery dV/dt ^c	dV/dt	5.0	V/ns
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Soldering recommendations (peak temperature) ^d	for 10 s	260	

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 28\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 2.6\text{ A}$ (see fig. 12)
c. $I_{SD} \leq 2.6\text{ A}$, $dI/dt \leq 70\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$
d. 1.6 mm from case
e. When mounted on 1" square PCB (FR-4 or G-10 material)

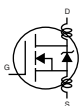
**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	-	110	°C/W
Maximum junction-to-ambient (PCB mount) ^a	R_{thJA}	-	-	50	
Maximum junction-to-case (drain)	R_{thJC}	-	-	5.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		200	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.30	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 1.6 A ^b	-	-	1.5	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 1.6 A ^b		0.80	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	140	-	pF
Output capacitance	C _{oss}			-	53	-	
Reverse transfer capacitance	C _{rss}			-	15	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 3.3 A, V _{DS} = 160 V, see fig. 6 and 13 ^b	-	-	8.2	nC
Gate-source charge	Q _{gs}			-	-	1.8	
Gate-drain charge	Q _{gd}			-	-	4.5	
Turn-on delay time	t _{d(on)}	V _{DD} = 100 V, I _D = 3.3 A, R _g = 24 Ω, R _D = 30 Ω, see fig. 10 ^b		-	8.2	-	ns
Rise time	t _r			-	17	-	
Turn-off delay time	t _{d(off)}			-	14	-	
Fall time	t _f			-	8.9	-	
Internal drain inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal source inductance	L _S			-	7.5	-	
Drain-source body diode characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	2.6	A
Pulsed diode forward current ^a	I _{SM}			-	-	10	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 2.6 A, V _{GS} = 0 V ^b		-	-	2.0	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 3.3 A, dI/dt = 100 A/μs ^b		-	150	310	ns
Body diode reverse recovery charge	Q _{rr}			-	0.60	1.4	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

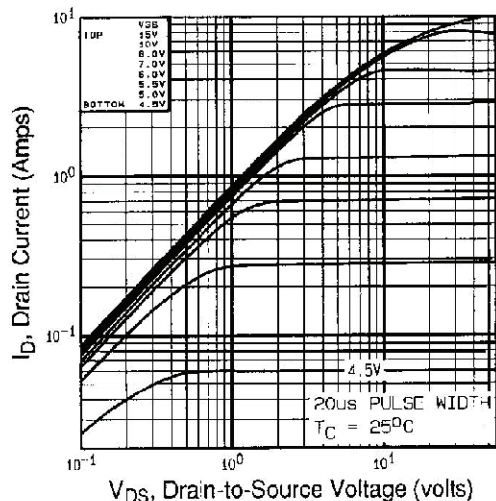


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$

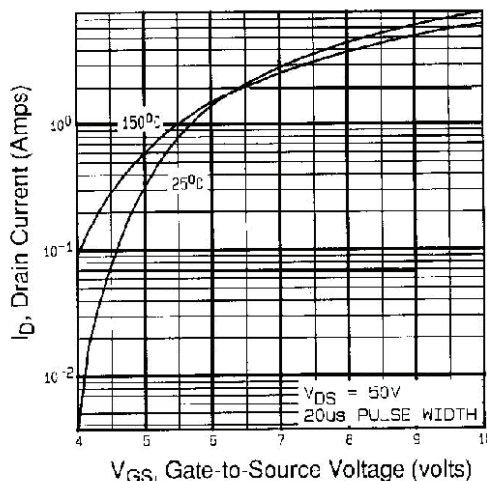


Fig. 2 - Typical Transfer Characteristics

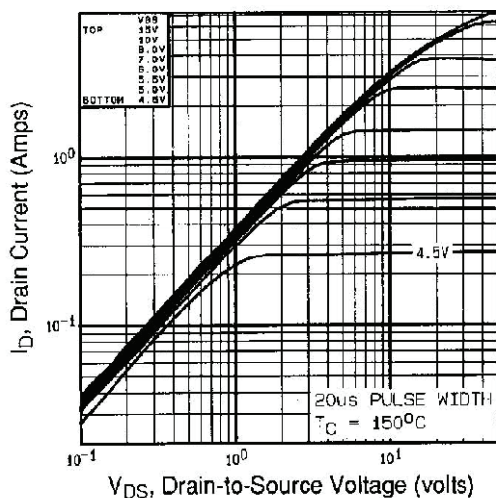


Fig. 1 - Typical Output Characteristics, $T_C = 150\text{ }^{\circ}\text{C}$

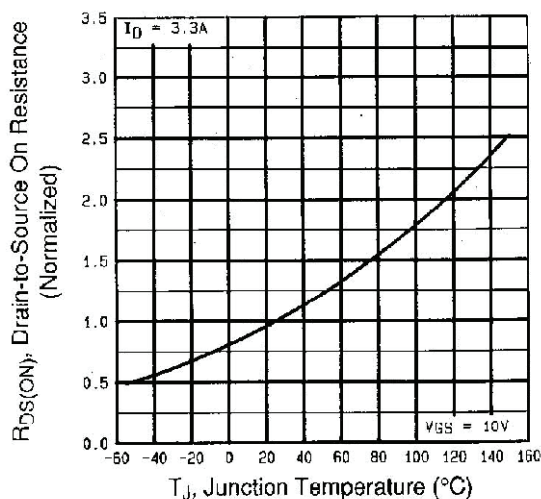
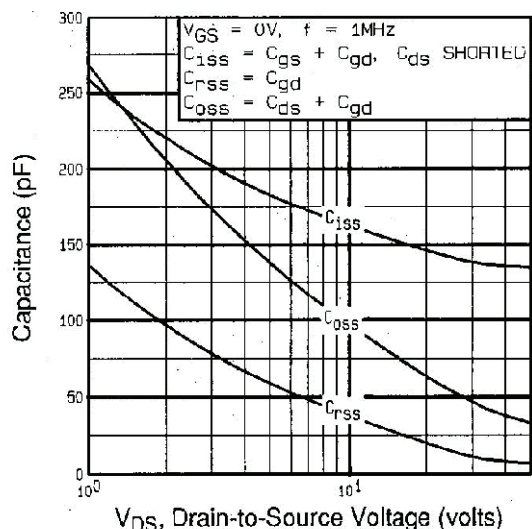
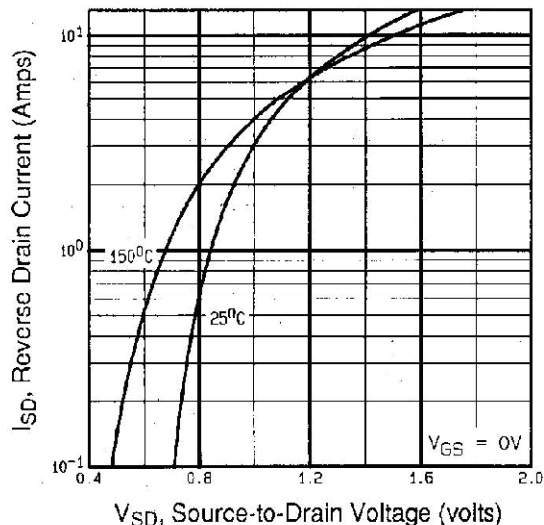
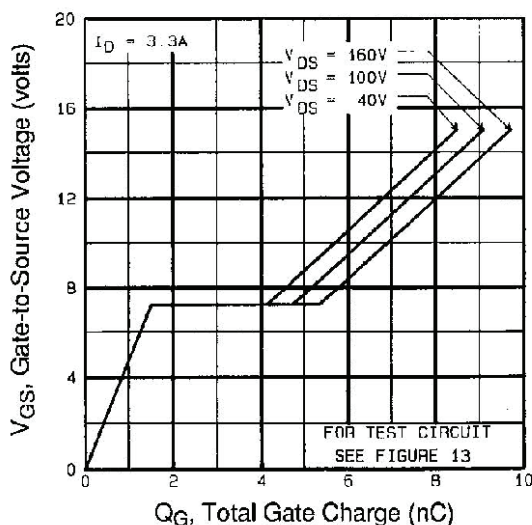
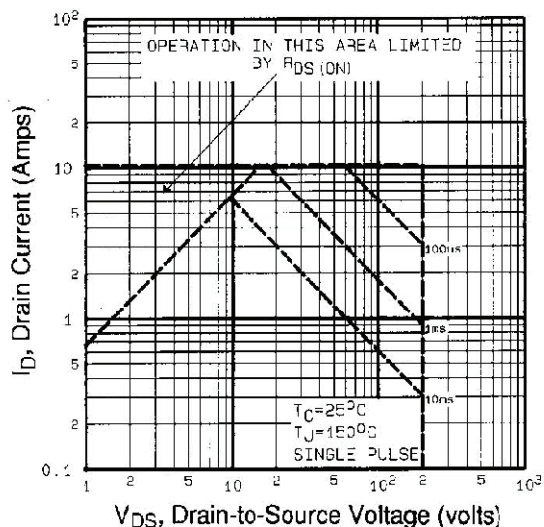


Fig. 3 - Normalized On-Resistance vs. Temperature


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 6 - Typical Source-Drain Diode Forward Voltage

Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 7 - Maximum Safe Operating Area

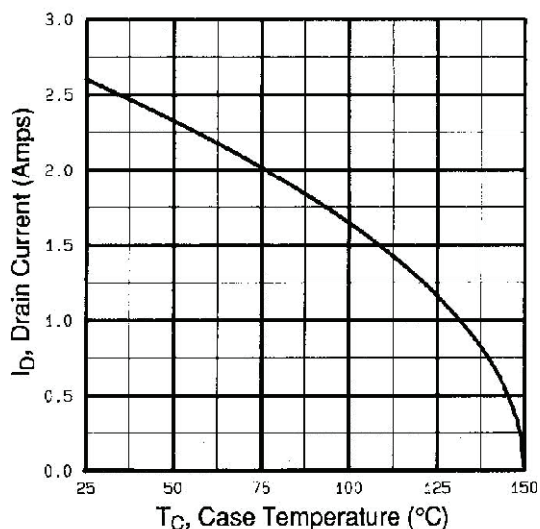


Fig. 8 - Maximum Drain Current vs. Case Temperature

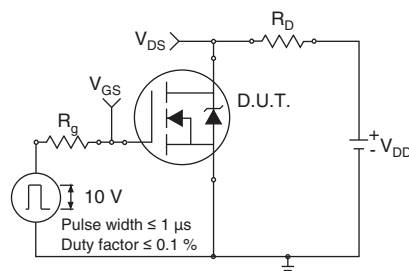


Fig. 10a - Switching Time Test Circuit

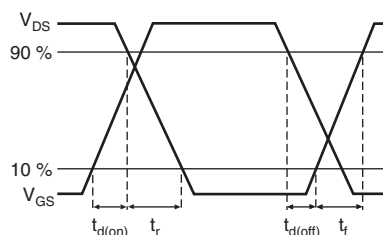


Fig. 10b - Switching Time Waveforms

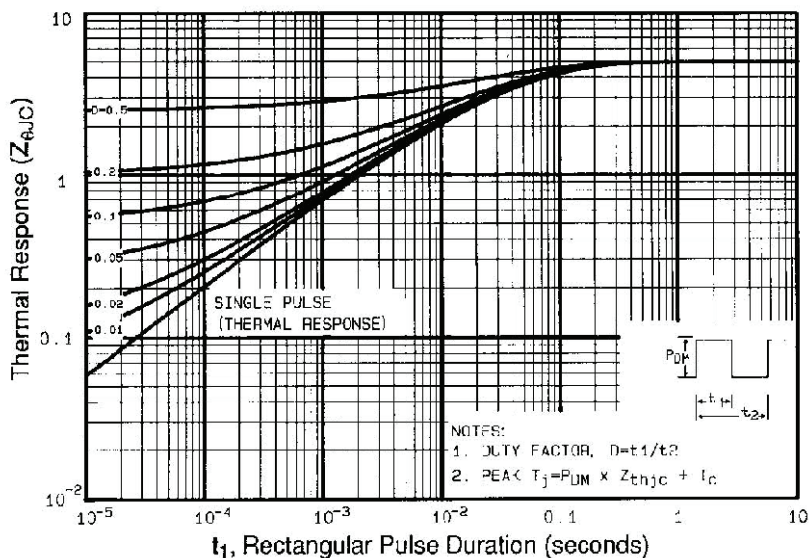


Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

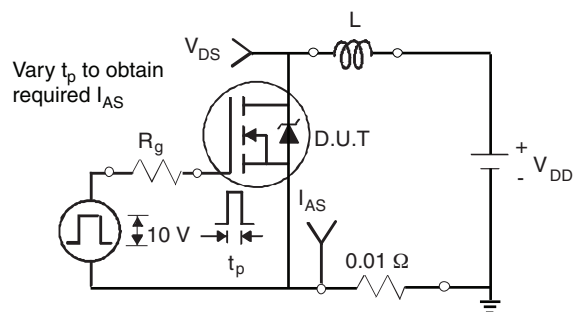


Fig. 12a - Unclamped Inductive Test Circuit

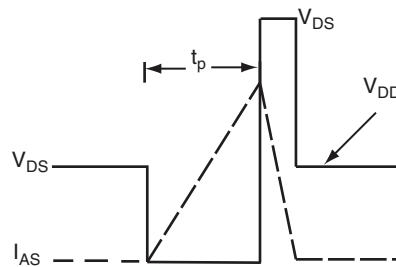


Fig. 12b - Unclamped Inductive Waveforms

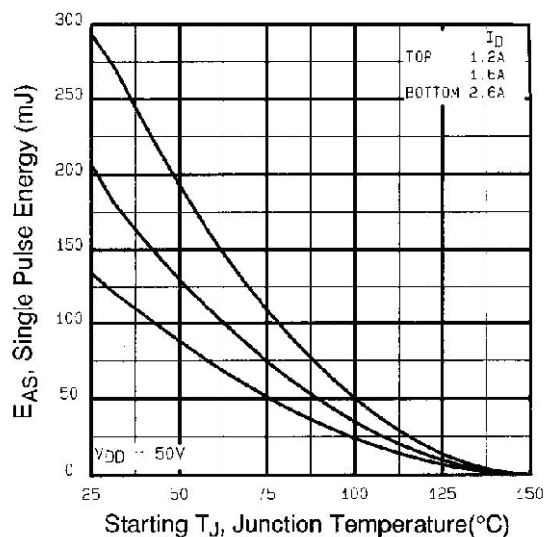


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

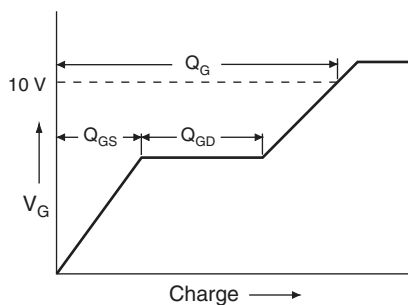


Fig. 13a - Basic Gate Charge Waveform

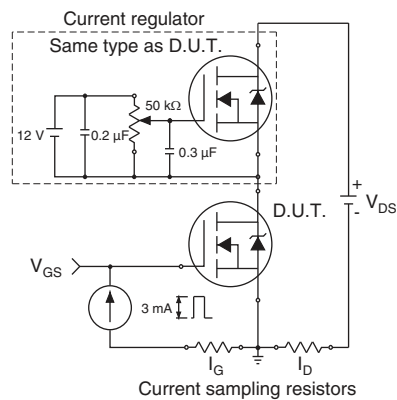
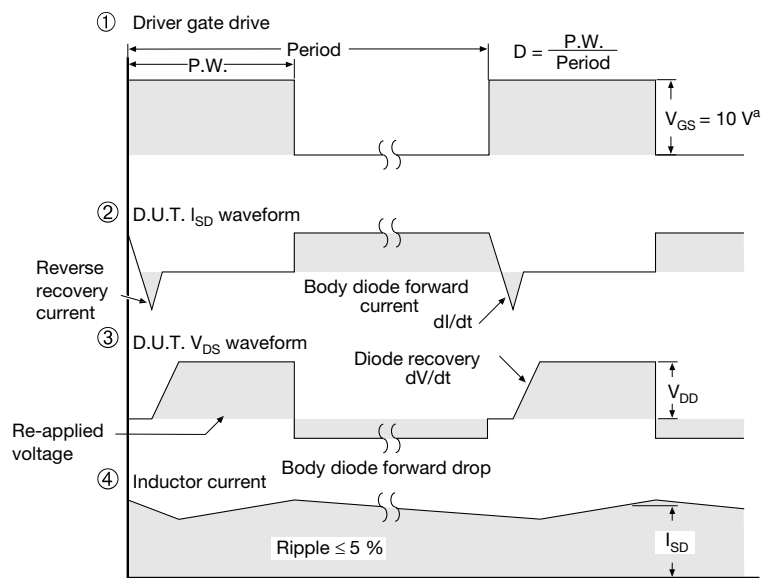
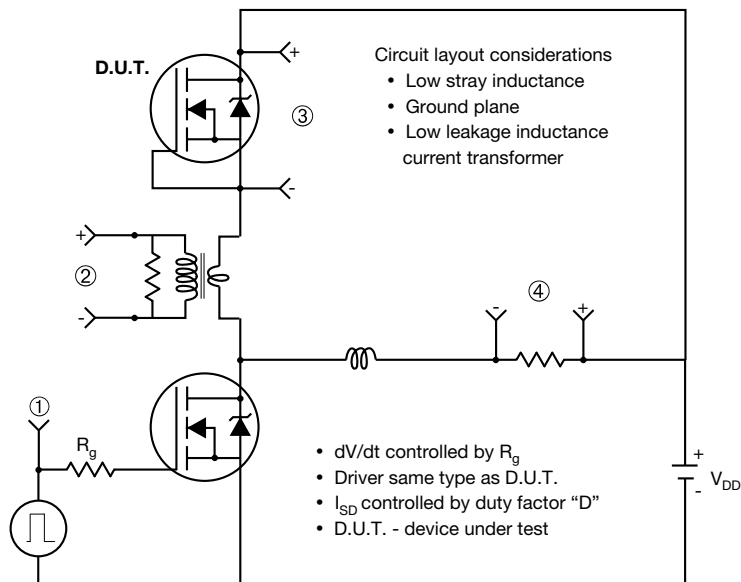


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 10 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91268.

TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

DIM.	MILLIMETERS	
	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
DWG: 5347

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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